

Sergey A. Kukushkin

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#	Paper	IF	Citations
233	Theory and practice of SiC growth on Si and its applications to wide-gap semiconductor films. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 313001	3	117
232	Thin-film condensation processes. <i>Uspekhi Fizicheskikh Nauk</i> , 1998 , 168, 1083	0.5	102
231	New phase formation on solid surfaces and thin film condensation. <i>Progress in Surface Science</i> , 1996 , 51, 1-107	6.6	95
230	Synthesis of epitaxial silicon carbide films through the substitution of atoms in the silicon crystal lattice: A review. <i>Physics of the Solid State</i> , 2014 , 56, 1507-1535	0.8	91
229	New method for growing silicon carbide on silicon by solid-phase epitaxy: Model and experiment. <i>Physics of the Solid State</i> , 2008 , 50, 1238-1245	0.8	84
228	A new method for the synthesis of epitaxial layers of silicon carbide on silicon owing to formation of dilatation dipoles. <i>Journal of Applied Physics</i> , 2013 , 113, 024909	2.5	81
227	Thin-film condensation processes. <i>Physics-Uspekhi</i> , 1998 , 41, 983-1014	2.8	78
226	Stress-driven nucleation of coherent islands: theory and experiment. <i>Applied Surface Science</i> , 2002 , 188, 156-162	6.7	64
225	Kinetic model of coherent island formation in the case of self-limiting growth. <i>Physical Review B</i> , 2001 , 64,	3.3	54
224	Raman Investigation of Different Polytypes in SiC Thin Films Grown by Solid-Gas Phase Epitaxy on Si (111) and 6H-SiC Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 359-362	0.4	44
223	First-order phase transition through an intermediate state. <i>Physics of the Solid State</i> , 2014 , 56, 792-800	0.8	34
222	Crystallization of thin polycrystalline PZT films on Si/SiO ₂ /Pt substrates. <i>Physics of the Solid State</i> , 2010 , 52, 132-136	0.8	34
221	Micro-Raman Mapping of 3C-SiC Thin Films Grown by Solid-Gas Phase Epitaxy on Si (111). <i>Nanoscale Research Letters</i> , 2010 , 5, 1507-1511	5	33
220	Evolution processes in multicomponent and multiphase films. <i>Thin Solid Films</i> , 1992 , 207, 302-312	2.2	33
219	Electron-microscopic investigation of a SiC/Si(111) structure obtained by solid phase epitaxy. <i>Technical Physics Letters</i> , 2008 , 34, 992-994	0.7	23
218	Nucleation of pores in brittle solids under load. <i>Journal of Applied Physics</i> , 2005 , 98, 033503	2.5	22
217	Nanoindentation of GaN/SiC thin films on silicon substrate. <i>Journal of Physics and Chemistry of Solids</i> , 2017 , 102, 151-156	3.9	21

216	Thin-film heteroepitaxy by the formation of the dilatation dipole ensemble. <i>Doklady Physics</i> , 2012 , 57, 217-220	0.8	20
215	Kinetics of first-order phase transitions in the asymptotic stage. <i>Journal of Experimental and Theoretical Physics</i> , 1998 , 86, 1201-1208	1	20
214	Growth and structure of GaN layers on silicon carbide synthesized on a Si substrate by the substitution of atoms: A model of the formation of V-defects during the growth of GaN. <i>Physics of the Solid State</i> , 2015 , 57, 1899-1907	0.8	19
213	Anisotropy of the solid-state epitaxy of silicon carbide in silicon. <i>Semiconductors</i> , 2013 , 47, 1551-1555	0.7	19
212	Perturbation theory in the kinetics of first-order phase transitions. <i>Journal of Chemical Physics</i> , 1997 , 107, 3247-3252	3.9	19
211	Diffusional coalescence of island films on the real crystal surface in the case of layer-by-layer growth of islands in an isolated system. <i>Acta Metallurgica Et Materialia</i> , 1993 , 41, 1237-1241		19
210	Plasma assisted molecular beam epitaxy of thin GaN films on Si(111) and SiC/Si(111) substrates: Effect of SiC and polarity issues. <i>Thin Solid Films</i> , 2018 , 646, 158-162	2.2	18
209	Pore- and delamination-induced mismatch strain relaxation and conditions for the formation of dislocations, cracks, and buckles in the epitaxial AlN(0001)/SiC/Si(111) heterostructure. <i>Physics of the Solid State</i> , 2015 , 57, 162-172	0.8	17
208	Structural and optical properties of high quality ZnO thin film on Si with SiC buffer layer. <i>Thin Solid Films</i> , 2012 , 520, 6836-6840	2.2	17
207	Epitaxial gallium oxide on a SiC/Si substrate. <i>Physics of the Solid State</i> , 2016 , 58, 1876-1881	0.8	17
206	Determining polytype composition of silicon carbide films by UV ellipsometry. <i>Technical Physics Letters</i> , 2016 , 42, 175-178	0.7	16
205	Nanoindentation and deformation properties of nanoscale silicon carbide films on silicon substrate. <i>Technical Physics Letters</i> , 2014 , 40, 1114-1116	0.7	16
204	Microscopic theory of epitaxial film growth on vicinal surfaces. <i>Thin Solid Films</i> , 1993 , 227, 119-127	2.2	16
203	Epitaxial growth of zinc oxide by the method of atomic layer deposition on SiC/Si substrates. <i>Physics of the Solid State</i> , 2016 , 58, 1448-1452	0.8	16
202	AlGaAs and AlGaAs/GaAs/AlGaAs nanowires grown by molecular beam epitaxy on silicon substrates. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 484003	3	15
201	SEM, Dielectric, Pyroelectric, and Piezoelectric Response of Thin Epitaxial AlN Films Grown on SiC/Si Substrate. <i>Ferroelectrics</i> , 2015 , 477, 121-130	0.6	15
200	Chloride vapor-phase epitaxy of gallium nitride on silicon: Effect of a silicon carbide interlayer. <i>Technical Physics Letters</i> , 2008 , 34, 479-482	0.7	15
199	The nucleation of coherent semiconductor islands during the Stranski-Krastanov growth induced by elastic strains. <i>Semiconductors</i> , 2002 , 36, 1097-1105	0.7	15

198	Kinetics of thin film nucleation from multi-component vapor. <i>Journal of Physics and Chemistry of Solids</i> , 1995 , 56, 831-838	3.9	15
197	Quantum mechanical theory of epitaxial transformation of silicon to silicon carbide. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 464006	3	14
196	Mechanism of the phase transformation of the pyrochlore phase into the perovskite phase in lead zirconate titanate films on silicon substrates. <i>Physics of the Solid State</i> , 2012 , 54, 611-616	0.8	14
195	The Gorsky effect in the synthesis of silicon-carbide films from silicon by topochemical substitution of atoms. <i>Technical Physics Letters</i> , 2017 , 43, 631-634	0.7	14
194	Nucleation of III nitride semiconductors in heteroepitaxy. <i>Physics of the Solid State</i> , 2001 , 43, 2229-2233	0.8	14
193	Self-organization in the formation of a nanoporous carbon material. <i>Physics of the Solid State</i> , 2000 , 42, 2314-2317	0.8	14
192	Soliton model of island migration in thin films. <i>Surface Science</i> , 1995 , 329, 135-140	1.8	14
191	Study of the Anisotropic Elastoplastic Properties of EGa ₂ O ₃ Films Synthesized on SiC/Si Substrates. <i>Physics of the Solid State</i> , 2018 , 60, 852-857	0.8	14
190	Semipolar AlN and GaN on Si(100): HVPE technology and layer properties. <i>Journal of Crystal Growth</i> , 2017 , 457, 202-206	1.6	13
189	Structural characterization of GaN epilayers on silicon: Effect of buffer layers. <i>Technical Physics Letters</i> , 2011 , 37, 326-329	0.7	13
188	Morphological stability of islands upon thin-film condensation. <i>Physical Review E</i> , 1996 , 53, 4964-4968	2.4	13
187	Phase equilibrium in the formation of silicon carbide by topochemical conversion of silicon. <i>Physics of the Solid State</i> , 2016 , 58, 747-751	0.8	13
186	Drift mechanism of mass transfer on heterogeneous reaction in crystalline silicon substrate. <i>Physica B: Condensed Matter</i> , 2017 , 512, 26-31	2.8	12
185	Studying Evolution of the Ensemble of Micropores in a SiC/Si Structure during Its Growth by the Method of Atom Substitution. <i>Physics of the Solid State</i> , 2019 , 61, 299-306	0.8	12
184	Thermodynamics and kinetics of switching effects in ferroelectrics. <i>Physical Review B</i> , 2002 , 65,	3.3	12
183	Crystallization of binary melts and decay of supersaturated solid solutions at the ostwald ripening stage under non-isothermal conditions. <i>Journal of Physics and Chemistry of Solids</i> , 1995 , 56, 1259-1269	3.9	12
182	Pyroelectric and piezoelectric responses of thin AlN films epitaxy-grown on a SiC/Si substrate. <i>Physics of the Solid State</i> , 2016 , 58, 967-970	0.8	12
181	The Mechanism of Growth of GaN Films by the HVPE Method on SiC Synthesized by the Substitution of Atoms on Porous Si Substrates. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P480-P486	2	12

180	Group-III-nitride-based light-emitting diode on silicon substrate with epitaxial nanolayer of silicon carbide. <i>Technical Physics Letters</i> , 2012 , 38, 297-299	0.7	11
179	A new mechanism of elastic energy relaxation in heteroepitaxy of monocrystalline films: Interaction of point defects and dilatation dipoles. <i>Mechanics of Solids</i> , 2013 , 48, 216-227	0.5	11
178	Theory of the Ostwald ripening in multicomponent systems under non-isothermal conditions. <i>Journal of Physics and Chemistry of Solids</i> , 1996 , 57, 195-204	3.9	11
177	Structural and elastoplastic properties of (upbeta)-(hbox {Ga}_{2}hbox {O}_{3}) films grown on hybrid SiC/Si substrates. <i>Continuum Mechanics and Thermodynamics</i> , 2018 , 30, 1059-1068	3.5	10
176	Growth and optical properties of filamentary GaN nanocrystals grown on a hybrid SiC/Si(111) substrate by molecular beam epitaxy. <i>Physics of the Solid State</i> , 2016 , 58, 1952-1955	0.8	10
175	Structural properties and parameters of epitaxial silicon carbide films, grown by atomic substitution on the high-resistance (111) oriented silicon. <i>Superlattices and Microstructures</i> , 2017 , 111, 899-911	2.8	10
174	Peculiarities of crystallization of thin ferroelectric films of lead zirconate titanate. <i>Technical Physics Letters</i> , 2011 , 37, 163-165	0.7	10
173	Elastic interaction of point defects in cubic and hexagonal crystals. <i>Physics of the Solid State</i> , 2016 , 58, 971-980	0.8	10
172	Effect of Chemical Treatment of a Silicon Surface on the Quality and Structure of Silicon-Carbide Epitaxial Films Synthesized by Atom Substitution. <i>Semiconductors</i> , 2018 , 52, 802-808	0.7	10
171	Hybrid GaAs/AlGaAs NanowireQuantum dot System for Single Photon Sources. <i>Semiconductors</i> , 2018 , 52, 462-464	0.7	9
170	Epitaxy of semipolar GaN on a Si(001) substrate with a SiC buffer layer. <i>Technical Physics Letters</i> , 2014 , 40, 386-388	0.7	9
169	Separation of IIIIV/SiC epitaxial heterostructure from a Si substrate and their transfer to other substrate types. <i>Semiconductors</i> , 2017 , 51, 396-401	0.7	9
168	Stability of the surface of an elastically strained multicomponent film in a system with chemical reactions. <i>Physics of the Solid State</i> , 2015 , 57, 2524-2531	0.8	9
167	Mechanism and kinetics of early growth stages of a GaN film. <i>Physics of the Solid State</i> , 2002 , 44, 1399-1408		9
166	Evolution processes in multicomponent and multiphase film growth from solutions. <i>Thin Solid Films</i> , 1994 , 239, 16-26	2.2	9
165	Photoelectric characteristics of silicon carbideSilicon structures grown by the atomic substitution method in a silicon crystal lattice. <i>Semiconductors</i> , 2017 , 51, 621-627	0.7	8
164	X-ray reflectometry and simulation of the parameters of SiC epitaxial films on Si(111), grown by the atomic substitution method. <i>Physics of the Solid State</i> , 2017 , 59, 1014-1026	0.8	8
163	Growing IIIIV Semiconductor Heterostructures on SiC/Si Substrates. <i>Technical Physics Letters</i> , 2019 , 45, 711-713	0.7	8

162	A New Type of Carbon Nanostructure on a Vicinal Si(111)-8° Surface. <i>Technical Physics Letters</i> , 2019 , 45, 201-204	0.7	8
161	On the Mechanism of the Vapor-Solid Growth of Au-Catalyzed GaAs Nanowires. <i>Semiconductors</i> , 2019 , 53, 350-360	0.7	8
160	Epitaxial growth of cadmium sulfide films on silicon. <i>Physics of the Solid State</i> , 2016 , 58, 629-632	0.8	8
159	Pendeo-epitaxy of stress-free AlN layer on a profiled SiC/Si substrate. <i>Thin Solid Films</i> , 2016 , 606, 74-79	2.2	8
158	Epitaxial silicon carbide on a 6° silicon wafer. <i>Technical Physics Letters</i> , 2014 , 40, 36-39	0.7	8
157	Infrared spectroscopy of silicon carbide layers synthesized by the substitution of atoms on the surface of single-crystal silicon. <i>Physics of the Solid State</i> , 2015 , 57, 2543-2549	0.8	8
156	TEM investigation of semipolar GaN layers grown on Si(001) offcut substrates. <i>Semiconductor Science and Technology</i> , 2015 , 30, 114002	1.8	8
155	Morphological stability criterion for a spherical crystallization front in a multicomponent system with chemical reactions. <i>Physics of the Solid State</i> , 2014 , 56, 2530-2536	0.8	8
154	Aluminum nitride on silicon: Role of silicon carbide interlayer and chloride vapor-phase epitaxy technology. <i>Technical Physics Letters</i> , 2010 , 36, 496-499	0.7	8
153	Diffusional coalescence of island films on the real crystal surface in the case of layer-by-layer growth of islands. An open system. Undamped sources of deposited atoms. <i>Acta Metallurgica Et Materialia</i> , 1993 , 41, 1243-1244		8
152	Mechanism of Formation of Carbon-Vacancy Structures in Silicon Carbide during Its Growth by Atomic Substitution. <i>Physics of the Solid State</i> , 2018 , 60, 1891-1896	0.8	8
151	Epitaxial Growth of Cadmium Selenide Films on Silicon with a Silicon Carbide Buffer Layer. <i>Physics of the Solid State</i> , 2018 , 60, 504-509	0.8	7
150	Properties of SiC Films Obtained by the Method of Substitution of Atoms on Porous Silicon. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P158-P160	2	7
149	HVPE growth of GaN in the semipolar direction on planar Si(210). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 433-436		7
148	IR spectra of carbon-vacancy clusters in the topochemical transformation of silicon into silicon carbide. <i>Physics of the Solid State</i> , 2017 , 59, 2430-2435	0.8	7
147	Evolution of the morphology of a micropore in a brittle solid under external stress. <i>Physics of the Solid State</i> , 2008 , 50, 1445-1449	0.8	7
146	Nonequilibrium heteroepitaxy of silicon carbide on silicon. <i>Technical Physics Letters</i> , 2005 , 31, 859	0.7	7
145	Semipolar GaN(1001) Epitaxial Layer Prepared on Nano-Patterned SiC/Si(100) Template. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800268	1.3	7

144	Carbon-Based Aromatic-Like Nanostructures on the Vicinal SiC Surfaces Induced by Ba Adsorption. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, M53-M59	2	6
143	Development of Burton- Cabrera- Frank Theory for the Growth of a Non-Kossel Crystal via Chemical Reaction. <i>Crystal Growth and Design</i> , 2020 , 20, 2590-2601	3.5	6
142	MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate 2016 ,		6
141	Sequential structural characterization of layers in the GaN/AlN/SiC/Si(111) system by X-ray diffraction upon every growth stage. <i>Technical Physics Letters</i> , 2013 , 39, 994-997	0.7	6
140	Evolution of the symmetry of intermediate phases and their phonon spectra during the topochemical conversion of silicon into silicon carbide. <i>Physics of the Solid State</i> , 2017 , 59, 28-33	0.8	6
139	Luminescence spectra of hexagonal forms of silicon carbide in mosaic films grown by solid-state epitaxy. <i>Physics of the Solid State</i> , 2009 , 51, 2469-2473	0.8	6
138	Kinetics of brittle fracture of elastic materials. <i>Physics of the Solid State</i> , 1998 , 40, 1147-1150	0.8	6
137	Perturbation methods in the kinetics of nanocluster growth. <i>Physics of the Solid State</i> , 2002 , 44, 2175-2188	0.8	6
136	Diffusional coalescence of island films on the real crystal surface in the case of layer-by-layer growth of islandsIV. Theory and experiment. <i>Acta Metallurgica Et Materialia</i> , 1994 , 42, 2803-2810		6
135	Epitaxial growth of cadmium telluride films on silicon with a buffer silicon carbide layer. <i>Physics of the Solid State</i> , 2017 , 59, 399-402	0.8	5
134	Role of elastic energy in the formation of ferroelectric barium strontium titanate films on sapphire. <i>Physics of the Solid State</i> , 2015 , 57, 815-819	0.8	5
133	A new insight into the mechanism of low-temperature Au-assisted growth of InAs nanowires. <i>CrystEngComm</i> , 2019 , 21, 4707-4717	3.3	5
132	Carrier mobility in undoped SiC layers grown on silicon by a new epitaxial technique. <i>Technical Physics Letters</i> , 2013 , 39, 488-491	0.7	5
131	Metal organic vapor phase epitaxy growth of (Al)GaN heterostructures on SiC/Si(111) templates synthesized by topochemical method of atoms substitution. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700190	1.6	5
130	Aluminum and gallium nitrides on a silicon substrate with an intermediate silicon carbide nanolayer for ultraviolet devices. <i>Journal of Optical Technology (A Translation of Opticheskii Zhurnal)</i> , 2011 , 78, 435	0.9	5
129	Type IIA photosensitivity and formation of pores in optical fibers under intense ultraviolet irradiation. <i>Journal of Applied Physics</i> , 2007 , 102, 053502	2.5	5
128	The Effect of pH on Nucleation Kinetics in Solutions. <i>Doklady Physical Chemistry</i> , 2001 , 377, 117-120	0.8	5
127	Crystallization of a eutectic Pb-Sn melt in the thermal field of a temperature gradient. <i>Physics of the Solid State</i> , 2001 , 43, 597-601	0.8	5

126	Study of SiC buffer layer thickness influence on photovoltaic properties of n-GaN NWs/SiC/p-Si heterostructure. <i>Materials Science in Semiconductor Processing</i> , 2019 , 90, 20-25	4.3	5
125	Spiral growth of a crystal due to chemical reaction. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 022006	0.6	5
124	Semipolar AlN on Si(100): Technology and properties. <i>Microelectronic Engineering</i> , 2017 , 178, 34-37	2.5	4
123	Photoelectric Properties of GaN Layers Grown by Plasma-Assisted Molecular-Beam Epitaxy on Si(111) Substrates and SiC/Si(111) Epitaxial Layers. <i>Semiconductors</i> , 2019 , 53, 180-187	0.7	4
122	Evolution of the morphology of diamond particles and mechanism of their growth during the synthesis by chemical vapor deposition. <i>Physics of the Solid State</i> , 2015 , 57, 2184-2190	0.8	4
121	Molecular dynamics simulation of the indentation of nanoscale films on a substrate. <i>Technical Physics Letters</i> , 2016 , 42, 639-643	0.7	4
120	Synchrotron-radiation photoemission study of the ultrathin Ba/3C/SiC(111) interface. <i>Journal of Physics and Chemistry of Solids</i> , 2016 , 90, 40-44	3.9	4
119	Misfit dislocation locking and rotation during gallium nitride growth on SiC/Si substrates. <i>Physics of the Solid State</i> , 2017 , 59, 674-681	0.8	4
118	Effect of the n and p-type Si(100) substrates with a SiC buffer layer on the growth mechanism and structure of epitaxial layers of semipolar AlN and GaN. <i>Physics of the Solid State</i> , 2015 , 57, 1966-1971	0.8	4
117	Theory of Phase Transformations in the Mechanics of Solids and its Applications for Description of Fracture, Formation of Nanostructures and Thin Semiconductor Films Growth. <i>Key Engineering Materials</i> , 2012 , 528, 145-164	0.4	4
116	The optical constants of zinc oxide epitaxial films grown on silicon with a buffer nanolayer of silicon carbide. <i>Journal of Optical Technology (A Translation of Opticheskii Zhurnal)</i> , 2011 , 78, 440	0.9	4
115	Self-organization in film nucleation in the high-T c superconductor Y-Ba-Cu-O system. <i>Physics of the Solid State</i> , 1997 , 39, 189-191	0.8	4
114	Phase transitions and the nucleation of catalytic nanostructures under the action of chemical, physical, and mechanical factors. <i>Kinetics and Catalysis</i> , 2008 , 49, 79-91	1.5	4
113	Photoluminescence spectra of n-ZnO/p-GaN:(Er + Zn) and p-AlGaN:(Er + Zn) heterostructures. <i>Semiconductors</i> , 2008 , 42, 766-771	0.7	4
112	Formation of pores in the optical fiber exposed to intense pulsed UV radiation. <i>Technical Physics</i> , 2006 , 51, 1035-1045	0.5	4
111	Thermodynamics and kinetics of the initial stages of polarization switching in ferroelectrics. <i>Physics of the Solid State</i> , 2001 , 43, 82-89	0.8	4
110	Theory of the late-stage crystallization of eutectic composition melts. <i>Journal of Physics and Chemistry of Solids</i> , 2000 , 61, 1337-1343	3.9	4
109	Theory of the Ostwald ripening of new-phase nuclei in single-component melts. <i>Acta Metallurgica Et Materialia</i> , 1995 , 43, 715-722		4

108	Growth of island films from binary melts or a vapor phase at the ostwald ripening stage under non-isothermal conditions. <i>Journal of Physics and Chemistry of Solids</i> , 1996 , 57, 601-614	3.9	4
107	Diffusional coalescence of island films on the real crystal surface in the case of layer-by-layer growth of islandsIII. Analysis of the model. <i>Acta Metallurgica Et Materialia</i> , 1994 , 42, 2797-2801		4
106	On the theory of non-isothermal coalescence (coarsening) in the decomposition of supersaturated solid solutions. <i>Journal of Physics and Chemistry of Solids</i> , 1992 , 53, 717-721	3.9	4
105	Determination of migration mechanisms and their influence on the structure of films. <i>Thin Solid Films</i> , 1992 , 221, 267-270	2.2	4
104	A new method for Synthesis of Epitaxial Films of Silicon Carbide on Sapphire Substrates (Al ₂ O ₃). <i>Reviews on Advanced Materials Science</i> , 2018 , 57, 82-96	4.8	4
103	A New Trigonal (Rhombohedral) SiC Phase: Ab Initio Calculations, a Symmetry Analysis and the Raman Spectra. <i>Physics of the Solid State</i> , 2018 , 60, 2066-2071	0.8	4
102	New Semipolar Aluminum Nitride Thin Films: Growth Mechanisms, Structure, Dielectric and Pyroelectric Properties. <i>Ferroelectrics</i> , 2019 , 544, 33-37	0.6	3
101	Two-Stage Conversion of Silicon to Nanostructured Carbon by the Method of Coordinated Atomic Substitution. <i>Physics of the Solid State</i> , 2019 , 61, 456-463	0.8	3
100	A quantum-mechanical model of dilatation dipoles in topochemical synthesis of silicon carbide from silicon. <i>Physics of the Solid State</i> , 2017 , 59, 1238-1241	0.8	3
99	GaN growth via HVPE on SiC/Si substrates: growth mechanisms. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 032028	0.3	3
98	Effect of SiC buffer layer on GaN growth on Si via PA-MBE. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 032038	0.3	3
97	Elastic interaction of point defects in crystals with cubic symmetry. <i>Mechanics of Solids</i> , 2013 , 48, 431-438.5		3
96	Kinetics of the initial stage in a first-order phase transformation in thin films. <i>Physics of the Solid State</i> , 1997 , 39, 104-108	0.8	3
95	Growth, structure, and morphological stability of nuclei growing from eutectic melts. <i>Physics of the Solid State</i> , 1997 , 39, 1299-1304	0.8	3
94	Self-organization in the process of multicomponent film nucleation. <i>Journal of Physics and Chemistry of Solids</i> , 1997 , 58, 1115-1118	3.9	3
93	Kinetics of pore formation upon plastic deformation of crystals with a cesium chloride structure. <i>Physics of the Solid State</i> , 2001 , 43, 270-273	0.8	3
92	Evolution of phase composition and associated properties in the process of growth of thin films. <i>Journal of Applied Physics</i> , 1999 , 86, 1370-1376	2.5	3
91	Kinetics of non-isothermal nucleation of thin films. <i>Journal of Physics and Chemistry of Solids</i> , 1995 , 56, 211-214	3.9	3

90	Anomalous Properties of the Dislocation-Free Interface between Si(111) Substrate and 3C-SiC(111) Epitaxial Layer. <i>Materials</i> , 2020 , 14,	3.5	3
89	Separation of stress-free AlN/SiC thin films from Si substrate. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012034	0.3	3
88	The use of SiC/Si(111) hybrid substrate for MBE growth of GaN nanowires. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012027	0.3	3
87	Photoemission studies of the vicinal SiC(100) 4 \times surface and the Cs/SiC(100) 4 \times interface. <i>Technical Physics Letters</i> , 2016 , 42, 1145-1148	0.7	3
86	The C 1s core level spectroscopy of carbon atoms at the surface SiC/Si(111)-4 \times layer and Cs/SiC/Si(111)-4 \times interface. <i>Semiconductors</i> , 2016 , 50, 1327-1332	0.7	3
85	Strength and structural properties of AlN films grown on SiC/Si substrates synthesized by atomic substitution. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012003	0.3	3
84	The use of SiC/Si hybrid substrate for MBE growth of thick GaN layers 2019 ,		3
83	Ascending Si diffusion into growing GaN nanowires from the SiC/Si substrate: up to the solubility limit and beyond. <i>Nanotechnology</i> , 2020 , 31, 294003	3.4	3
82	Structural heteroepitaxy during topochemical transformation of silicon to silicon carbide. <i>Physics of the Solid State</i> , 2017 , 59, 773-779	0.8	2
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